

Abstract

A method for producing etched holes and/or etched trenches (11) of components based on silicon and/or a layered silicon/insulator structure is described. A germanium-containing layer and/or a germanium layer (9) is provided at the point in 5 the etching direction at which or in whose surroundings an etching procedure is to be completed. Germanium and/or germanium compounds are detected during the etching procedure and the etching procedure is controlled, in particular interrupted, as a function of the detection of germanium and/or germanium compounds. In addition, a diaphragm sensor unit is described, in whose layered structure a 10 germanium and/or germanium-containing layer is provided